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TI - METHOD AND APPARATUS FOR WRITING OPTICAL DISK

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- Method and apparatus for writing optical disk

- KR2003069706 NOVELTY - A method and an apparatus for writing an optical disk are provided to select the optimum signal write strategy and write power for write characteristics of the optical disk.

- DETAILED DESCRIPTION A manufacturer of a loaded optical disk is discriminated(\$300-\$330). In the case that the manufacturer is preliminarily stored in a memory, a microcomputer reads a reference write power and signal write strategy from signal write characteristic information, executes optical power control for deciding the optimum write power, and writes data according to the decided optimum write power and the signal write strategy(\$350-\$390). In the case that the manufacturer is not preliminarily stored in the memory, the microcomputer confirms physical characteristics of the optical disk(\$340). In the case that the manufacturer is not discriminated, test writes are executed with power scan by using signal write strategies and write powers included in default signal write characteristic information preliminarily set(\$400-\$440). Based on the write characteristic of the optical disk, the optimum write power is decided in the scan write power. Based on the write characteristic of the optical disk, the optimum signal write strategy is decided in the signal write strategies included in the default signal write characteristic information.
- (Dwg.1/10)
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